

## ABSTRACT

An etching method includes a step (a) of providing a substrate, the substrate including a first film and a second film having an opening on the first film, the first film containing a metallic element and a non-metallic element, a step (b) of forming a protective film on a sidewall of a recess formed in the first film corresponding to the opening, and a step (c) of etching the first film through the opening with a plasma generated from a processing gas including a halogen-containing gas at the same time as or after the step (b).

FIG. 14